

Smart Low Side Power Switch

HITFET® BTS3408G





Datasheet Rev. 1.3

Features

- Logic Level Input
- · Compatible to 3V micro controllers
- ESD protection
- · Thermal shutdown with auto restart
- · Overload protection
- Short circuit protection
- Over voltage protection
- Open load detection (during Off)
- Current limitation
- · Direct parallel control of the inputs
- FREEZE functionality for multiplexing
- · General fault flag
- · Very low standby guiescent current
- Switching frequencies up to 50kHz
- Green Product (RoHS compliant)
- AEC Qualified

Application

- All kinds of resistive, inductive and capacitive loads in switching applications
- μC compatible power switch for 12 V, 24 V and 42 V applications
- · Replaces electromechanical relays and discrete circuits
- · Line, stepper motor, lamp and relay driver

General Description

The BTS3408G is a dual channel Low-Side Switch with D-MOS output stages for driving resistive, capacitive and inductive loads. The design is based on Infineons Smart Power Technology (SPT) which allows bipolar, CMOS and power D-MOS devices on the same monolithic circuit.

The BTS3408G is protected by embedded protection functions and designed for automotive and industrial applications. It is especially suited for driving stepper motors and lines.

Туре	Ordering Code	Package
HITFET® BTS3408G	on request	PG-DSO8-36





Product Summary

Parameter	Symbol	Value	Unit
Supply voltage	V_{S}	4.5 - 60	V
Continuous drain source voltage	V_{DS}	60	V
On-state resistance	$R_{DS(ON)}$	550	mΩ
Current limitation	$I_{D(lim)}$	1	Α
Nominal output current (individual channel)	$I_{D(Nom)}$	0.55	Α
Clamping energy	E_{AS}	800	mJ

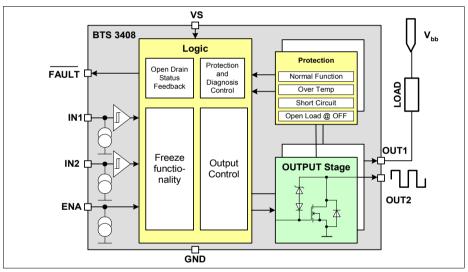


Figure 1 Block Diagram

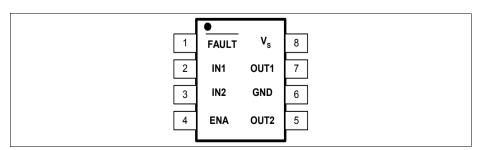


Figure 2 Pin Configuration



Pin Definitions and Functions

Pin	Symbol	Function
1	FAULT	General Fault Flag; see Table 2 for operation mode.
2	IN1	Input 1; input of channel 1; has an internal pull down; TTL/CMOS compatible input.
3	IN2	Input 2; input of channel 2; has an internal pull down; TTL/CMOS compatible input.
4	ENA	Enable/Freeze ; has an internal pull down; device is enabled when voltage is higher then 1.2 Volts; if the voltage is below 1.7 Volts the output is freezed, input signals will be ignored; if the voltage is above 2 Volts input signals will be output; see Table 1 for detailed information.
5	OUT2	Output 2; output of D-MOS stage 2.
6	GND	Ground.
7	OUT1	Output 1; output of D-MOS stage 1.
8	V_{S}	Power supply.

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Circuit Description

Logic Supply

The logic is supplied with 4.5 up to 60 Volt by the V_S pin. If V_S falls below max. 4.5 Volts the logic is shut down and the output stages are switched off.

Direct Inputs

ENA

The ENA/FREEZE input can be used to enable and/or to freeze the output control of the IC or to cut off the complete IC.

By pulling the ENA input to low, i.e. applying a Voltage V_{ENAL} , the IC is in disable mode. The power stages are switched off and the current consumption is reduced to $I_{S(stby)}$.

By applying a Voltage V_{ENAFZ} , the IC is in FREEZE mode. The output signals will remain in their former state. All input signals will be ignored.

By pulling the input to high, the IC is in Enable mode. All input signals are output.

The ENA - pin has an internal pull-down.

IN1 / IN2

Each output is independently controlled via the respective input pin. The input pins are high active. If the common enable pin is high, the individual input signals are output. The input pins have an internal pull-down.

Table 1 Functional Table

V _{ENA}	Mode	IN1	IN2	IN1(-1)	IN2(-1)	OUT1	OUT2	Comment
≤0.8V	Disable	X 1)	X 1)	X 1)	X 1)	L	L	all outputs OFF
1.2 1.7V	Freeze	X 1)	X 1)	L	L	L	L	former output state
1.2 1.7V	Freeze	X 1)	X 1)	L	Н	L	Н	former output state
1.2 1.7V	Freeze	X 1)	X 1)	Н	L	Н	L	former output state
1.2 1.7V	Freeze	X 1)	X 1)	Н	Н	Н	Н	former output state
≥2.0V	Enable	L	L	X 1)	X 1)	L	L	input is output
≥2.0V	Enable	L	Н	X 1)	X 1)	L	Н	input is output
≥2.0V	Enable	Н	L	X 1)	X 1)	Н	L	input is output
≥2.0V	Enable	Н	Н	X 1)	X 1)	Н	Н	input is output

¹⁾ X = not relevant

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Power stages

Each output is protected by embedded protection functions. In the event of an overload or short to supply, the current is internally limited. The current limit is set to $I_{D(lim)}$. If this operation leads to an overtemperature condition, a second protection level (about 165 $^{\circ}\text{C}$) will turn the effected output into a PWM-mode (selective thermal shutdown with restart) to prevent critical chip temperatures. The temperature hysteresis is typically 10K.

Zener clamping is implemented to limit voltages at the power transistors when inductive loads are switched off.

Diagnostic

The general FAULT pin is an open drain output. The FAULT pin is low active. It signals fault conditions of any of the two output stages. By doing so, single and/or dual fault conditions can be monitored. Single fault conditions can be assigned.

Table 2 Diagnostic Table

Operating Condition	ENA	IN _x	OUT _X	FAULT
Standby	L	X 1)	OFF	Н
Normal function	Н	Н	ON	Н
Over temperature	Н	Н	OFF 2)	L
Open load / short to ground	Н	L	OFF	L

¹⁾ X = not relevant

Fault Distinction

Open load / short to ground is recognized during OFF-state. Overtemperature as a result of an overload or short to battery can only arise during ON-state. If there is only one fault at a time, it is possible to distinguish which channel is affected with which fault.

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²⁾ selective thermal shutdown for each channel at overtemperature



Absolute Maximum Ratings ¹⁾ $T_{\rm i}$ = -40°C to 150°C , unless otherwise specified

Parameter	Symbol	Values	Unit	Remarks
Supply Voltage	V_{S}	+4.5 +60	٧	_
Drain source voltage (OUT1, OUT2)	V_{DS}	-0.3 +60	٧	_
Input voltage (IN1, IN2, ENA)	V_{IN}	-0.3 +7	٧	_
Continuous input current V _{IN} >7V	I_{IN}	1	mA	_
FAULT output voltage	V_{Fault}	-0.3 +7	٧	_
Operating temperature range Storage temperature range	$T_{ m stg}$	-40 +150 -55 +150		_
Power dissipation (DC) ²⁾	P_{tot}	0.88	W	_
Nominal load current ²⁾ one channel active both channel active	$I_{D(Nom)}$	0.55 0.45	Α	$V_{\rm DS} \le 0.5 \text{V},$ $T_{\rm i} \le 150 ^{\circ} \text{C},$ $T_{\rm A} = 85 ^{\circ} \text{C},$ $V_{\rm IN} = 5 \text{V}$
Unclamped single pulse inductive energy one channel active	E_{AS}	800	mJ	I_{D} =0.7A, $T_{j(start)}$ =25°C
Electrostatic discharge voltage (Human Body Model) according to MIL STD 883D, method 3015.7 and EOS/ESD assn. standard S5.1 - 1993	V_{ESD}	2000	V	_

Thermal Resistance

Junction soldering point	R_{thJS}	≤ 10	K/W	-
Junction - ambient @ min. footprint	R_{thJA}	≤ 185	K/W	_
Junction - ambient @ 6cm2 cooling area 2)		≤ 142		

Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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²⁾ Device on epoxy pcb 40 mm \times 40 mm \times 1.5 mm with 6 cm² copper area for pin 4 connection.



Electrical Characteristics

 $V_{\rm S}$ = 4.5 to 18V; $T_{\rm j}$ = -40 to 150°C; unless otherwise specified

Parameter	Sym-	Limit Values			Unit	Test Conditions
	bol	min.	typ.	max.		

Power supply

Supply voltage	V_{S}	4.5	_	60	٧	_
Supply current in enable mode	$I_{S(ON)}$	_	1.5	4	mA	ENA=High, OUT1=OUT2=On
Supply current in standby mode 1)	$I_{S(stby)}$	_	_	16	μΑ	ENA=Low

Power outputs

Drain source clamp voltage	$V_{\mathrm{DS(AZ)}}$	60	_	75	V	$I_{\rm D}$ = 1 mA
Output leakage current 2)	I_{DSS}	-	1	5	μΑ	$\begin{split} & ENA \!\!=\!\! Low, \\ & IN \!\!=\!\! Low, \\ & V_{DS} = 60 \; V \end{split}$
Output pull down current	$I_{\mathrm{PD(OL)}}$	50	100	200	μΑ	$\begin{aligned} & ENA \!\!=\!\! High, \\ & IN \!\!=\!\! Low, \\ & V_{DS} = 42\; V \end{aligned}$
On-state resistance	$R_{\mathrm{DS(on)}}$				$m\Omega$	$I_{\rm D} = 0.2 {\rm A},$
$T_{\rm j}$ = 25 °C	- (- /	_	480	550		$V_{\rm S}$ = 5 V
$T_{\rm j} = 150~{\rm ^{\circ}C}$		_	800	1000		
Current limit	$I_{D(lim)}$	1	1.5	2	Α	_
Turn-on time IN=High to 90% $I_{\rm D}$:	t _{on}	_	2	8	μs	$\begin{aligned} R_{\mathrm{L}} = & 2\mathrm{k}\Omega, \\ V_{\mathrm{BB}} = & 12\mathrm{V}, V_{\mathrm{S}} = & 5\mathrm{V} \end{aligned}$
Turn-off time IN=Low to 10% $I_{\rm D}$:	t _{on}	_	2	8	μs	$R_{\rm L}$ =2k Ω , $V_{\rm BB}$ =12V, $V_{\rm S}$ =5V

Digital inputs (IN1, IN2, ENA)

Input 'Low' voltage IN1, IN2: ENA:	$V_{INL} \ V_{ENAL}$	-0.3 -0.3	_ _	0.8 0.8	V	_
ENA voltage for 'FREEZE' functionality	V_{ENAFZ}	1.2	-	1.7	٧	_

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Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 4.5 to 18V; $T_{\rm i}$ = -40 to 150°C; unless otherwise specified

Parameter	Sym-	Limit Values			Unit	Test Conditions
	bol	min.	typ.	max.		
Input 'High' voltage					٧	_
IN1, IN2:	V_{INH}	2.0	_	-		
ENA:	V_{ENAH}	2.0	_	-		
Input voltage hysteresis	V_{INhys}	_	300	_	mV	_
Input pull down current					μΑ	_
IN1, IN2:	I_{INPD}	20	50	100		
ENA:	I_{ENAPD}	20	50	100		

Digital Output (FAULT)

Output 'Low' voltage	V_{FLTL}	_	_	0.4	V	$I_{FLTL} = 1.6 mA,$

Diagnostic Functions

Open load / short to ground detection voltage	$V_{ m DS(OL)}$	0.5*V _S	0.7*V _S	0.9*V _S	V	_
Fault filter time for open load	$t_{\rm filter(OL)}$	30	100	200	μs	$V_{\rm S}$ =5V

Protection Functions 3)

Thermal overload trip	T_{jt}	150	165	180	°С	_
temperature						
Thermal hysteresis	$\Delta T_{\rm jt}$	_	10	_	K	_
Unclamped single pulse inductive	E_{AS}				mJ	$I_{\rm D}\!\!=\!\!0.7~{\rm A}$
energy						
one channel active, T _{j(start)} =25°C				800		
both channel active, $T_{j(\text{start})}$ =25°C				550		
one channel active, $T_{i(start)}^{j(start)} = 150^{\circ}$ C				240		
both channel active, $T_{j(start)}$ =150°C				240		

¹⁾ See also diagram 4 on page 14.

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²⁾ See also diagram 5 on page 14.

³⁾ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.



EMC-Characteristics

The following EMC-Characteristics outline the behavior of typical devices. They are not part of any production test.

Table 3 Test Conditions

Parameter	Symbol	Value	Unit	Remark	
Temperature	T _A	23 ±5	°C	_	
Supply Voltage	V_{BB}	13.5	V	_	
Input Voltage (ENA, IN1, IN2)	V_{INx}	5	V	_	
Load	$R_{\text{L1}}, R_{\text{L2}}$	27	Ω	ohmic	
Operation mode	PWM DC		_ _	f _{INx} =100Hz, <i>D</i> =0.5 ON / OFF	
DUT specific	all tests with ENA=HIGH				

Fast electrical transients

acc. to ISO 7637

			Test F	Pulse Cycle Time and Generator Impedance			
Test ¹⁾ Max. Pulse Level		V _s and OUT _x stressed			OUT _x s	tressed	
	Level	ON	OFF	ON	OFF	impedance	
1	-200V	E(-120V)	E(-120V)	С	С	500ms ; 10 Ω	
2	+200V	E(+120V	E(+120V	С	С	500ms ; 10Ω	
3a	-200V	С	С	С	С	100ms ; 10Ω	
3b	+200V	С	С	С	С	100ms ; 10Ω	
4	-7V	С	С	С	С	0.01Ω	
5	175V	E(50V)	E(65V)	E(70V)	E(75V)	400ms ; 2Ω	

¹⁾ The test pulses are applied at V_{BB}

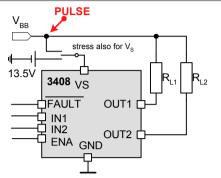
Definition of functional status

Class	Content
С	All functions of the device are performed as designed after exposure to disturbance.
E	One or more function of a device does not perform as designed after exposure and can not be returned to proper operation without repairing or replacing the device. The value after the character shows the limit.

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Conducted Emissions

Acc. IEC 61967-4 ($1\Omega/150\Omega$ method)

Typ. OUT_x Emissions at PWM-mode with 150 Ω -matching network

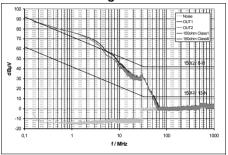
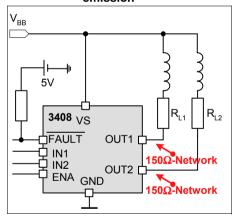


Figure 4 Test circuit for conducted emission 1)



Conducted Susceptibility

Acc. I47A/658/CD IEC 62132-4 (Direct Power Injection)

Direct Power Injection: Forward Power CW

Failure Criteria: Amplitude or frequency variation max. 10% at OUT

Typ. OUT_x Susceptibility at DC-ON/OFF and at PWM

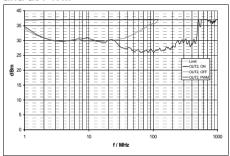
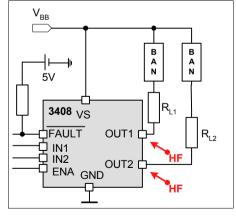


Figure 5 Test circuit for conducted susceptibility ²⁾



¹⁾ For defined decoupling and high reproducibility a defined choke (5µH at 1 MHz) is inserted between Vbb and Out-Pin.

Broadband Artificial Network (short BAN) consists of the same choke (5µH at 1 MHz) and the same 150ohm-matching network as for emission measurement for defined decoupling and high reproducibility.



Terms

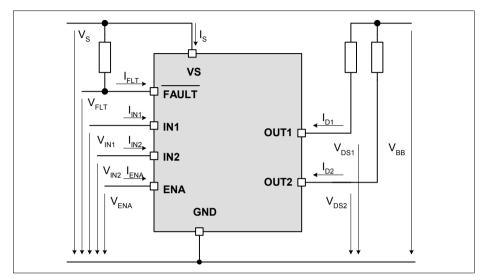
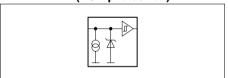


Figure 6 Input circuit (ESD protection)



ESD zener diodes are not designed for DC current.

Figure 7 Inductive and over voltage output clamp

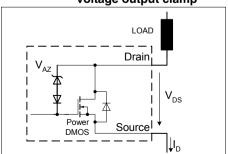
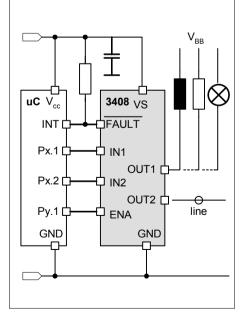


Figure 8 Application Circuit





Timing diagrams

Figure 9 Switching a resistive load

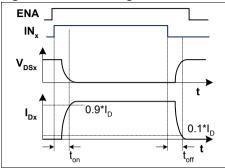


Figure 10 Switching an inductive load

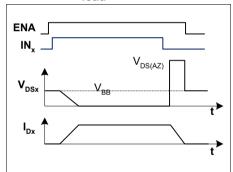
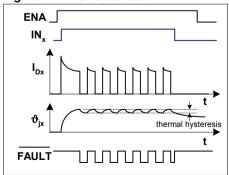
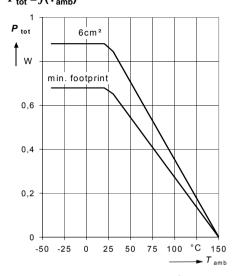


Figure 11 Short circuit



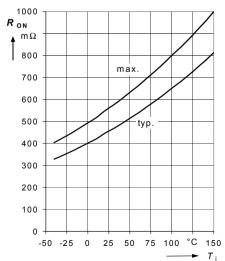
Characteristics

1. Max. allowable Power Dissipation $P_{\text{tot}} = f(T_{\text{amb}})$



2. On-state Resistance $R_{ON} = f(T_j)$;

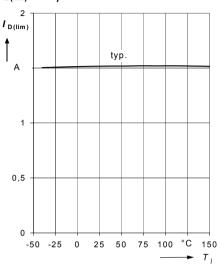
 $I_{\rm D}$ = 0.2 A; $V_{\rm S}$ = 5 V





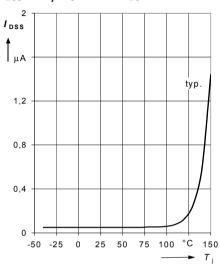
3. Typ. Short Circuit Current

$$I_{D(lim)} = f(T_i)$$



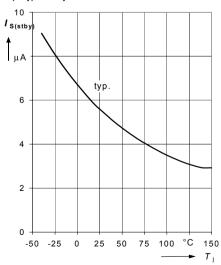
5. Typ. Output leakage current

$$I_{DSS} = f(T_i); V_S = 18 \text{ V}; V_{DS} = 60 \text{ V}$$



4. Typ. Supply current in Standby mode

$$I_{S(stby)} = f(T_i); V_S = 5 \text{ V}$$







Package Outline

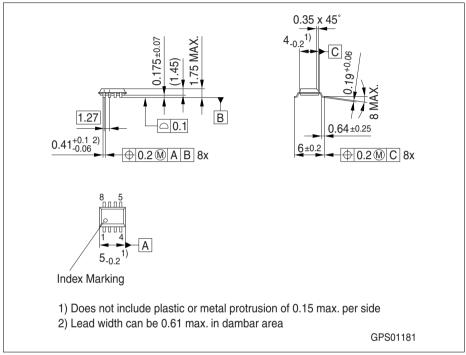


Figure 12 PG-DSO8-36 (Plastic Green Dual Small Outline Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Sorts of Packing

Package outlines for tubes, trays etc. are contained in our

SMD = Surface Mounted Device

Dimensions in mm



Revision History

Version	Date	Changes
Rev. 1.3	2008-01-09	Changed package outline drawing, updated package name
Rev. 1.2	2007-06-15	Released automotive green version Package parameter (humidity and climatic) removed in Maximum ratings AEC icon added RoHS icon added Green product (RoHS-compliant) added to the feature list AEC Stress Test Qualification added to the feature list Package information updated to green Green explanation added removed order number
Rev. 1.1	2005-10-10	Released production version

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